East Search for paper No. 0705

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	23	("20010004332"|"20020000606"|"20020142569"|"20030194853"|"5768192"|"6011725"|"6030871"|"6127227"|"6201282"|"6215148"|"6309927"|"6348711"|"6538292"|"6551880"|"6552387"|"6566699"|"6576511"|"6580124"|"6596590"|"6602805"|"6605839"|"6642113"|"6649971").PN.	US-PGPUB; USPAT	OR	ON	2005/07/14 11:18
S2	2	("5734185" "6248633").pn. jp-2001156188-$.did.	US-PGPUB; USPAT	OR	ON	2005/07/13 11:08
S3	6	("5734185" "6248633").pn. jp-2001156188-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/13 11:25
S4	126	(pizarro and (marcos marcus)).xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/13 12:45
S5	8908	(hfo2 "hfo.sub.2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 12:45
S6	385	S5 and trapping	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 12:45
S7	247	S6 and source and drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 12:46
S8	246	S6 and source same drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 12:46
S9	69	S7 and (atomic adj layer adj deposition ald atomic adj layer adj chemical adj vapor adj deposition alcvd al-cvd atomic-layer adj chemival adj vapor adj deposition atomic-layer adj cvd)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 14:05

S10	188	(multi adj bit multi-bit 2-bit two-bit two adj bit) and (hfo2 "hfo.sub.2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:39
S11	179	S10 and source and drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 14:05
S12	26	S11 and (atomic adj layer adj deposition ald atomic adj layer adj chemical adj vapor adj deposition alcvd al-cvd atomic-layer adj chemival adj vapor adj deposition atomic-layer adj cvd)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 14:27
S13	2	(increase with trapping adj (site center) with (implantation plasma))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 14:29
S14	28	trapping adj (site center) with (implantation plasma)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:33
S15	1	trapping adj (site center) with (implantation plasma) and (hfo2 "hfo.sub.2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:28
S16	11	("6674138" "6794764" "6804136" "6451641" "20040108537").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 14:35
S17	9	(multi adj bit multi-bit 2-bit two-bit two adj bit) and (hfo2 "hfo.sub.2" hafnium adj oxide) and angle with implantation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:43

S18	5	(multi adj bit multi-bit 2-bit two-bit two adj bit) and angle with implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:46
S19	1	257/324.cor. and angle with implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:47
S20	5	257/324 and angle with implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:48
S21	1	"257"/$3 and advantage with angle with implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:49
S22	2	advantage with angle with implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:49
S23	45	(increase decrease lower improve inhibit avoid eliminate allow permit) with angle with implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:50
S24	42	trapping with increase with (implantation plasma)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:37
S25	1242	trapping adj layer trapping-layer and (implantation plasma)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:38

S26	433	(trapping adj layer trapping-layer) and (implantation plasma)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:38
S27	133	(trapping adj layer trapping-layer) and (implantation plasma) and (multi adj bit multi-bit 2-bit two-bit two adj bit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:39
S28	39	(trapping adj layer trapping-layer) same (implantation plasma) and (multi adj bit multi-bit 2-bit two-bit two adj bit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:51
S29	43	trapping with (implantation plasma) and (multi adj bit multi-bit 2-bit two-bit two adj bit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:53
S30	12	trapping with (site center) with (create generate form) and (multi adj bit multi-bit 2-bit two-bit two adj bit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:56
S31	18	trapping with (site center) with (create generate form) with layer and "257"/$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:03
S32	14	S31 not S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:56
S33	5	trapping with (site center) with (induced induce) with layer and "257"/$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:04

S34	9	trapping with (site center) with (created generated) with layer and "257"/$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:06
S35	5	plasma with (oxygen nitrogen hydrogen) with trapping with (site center)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:07
S36	56	plasma with (oxygen nitrogen hydrogen) with trapping	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:08
S37	0	plasma with (oxygen nitrogen hydrogen) with trapping adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:08
S38	7	plasma with (oxygen nitrogen hydrogen) with trapping with charge	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:08
S39	11	(post-anneal post-annealing anneal annealing) with (stoichiometric densify densification) same (hfo2 "hfo.sub.2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:33
S40	52	angle adj implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:14
S41	171	densification with metal adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:14

S42	1	densification with metal adj oxide with improve	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:15
S43	4	densification with metal adj oxide with mechanical	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:16
S44	32	densification with metal adj oxide and (hfo2 "hfo.sub.2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:20
S45	35	densification with (hfo2 "hfo.sub. 2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:24
S46	0	densification with vacant and (hfo2 "hfo.sub.2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:24
S47	0	densification with fill with vacant and high-k	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:24
S48	0	densification with fill with vacant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:24
S49	0	densification with vacant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:25

S50	207	densification with fill	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:25
S51	14	densification with fill with oxygen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:25
S52	1217	plasma same nitrogen same exposure	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 11:19
S53	3	S52 same charge same trap$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 11:19